

Direct Evaluation for **Solid State Drive**

SMART TESTER *for* PCIe Series

EDSFF (E1.S, E1.L, E3.S) Supported.

SMART TESTER for PCIe G4
【Support Interface PCIe Gen 4 x 4 Lane】

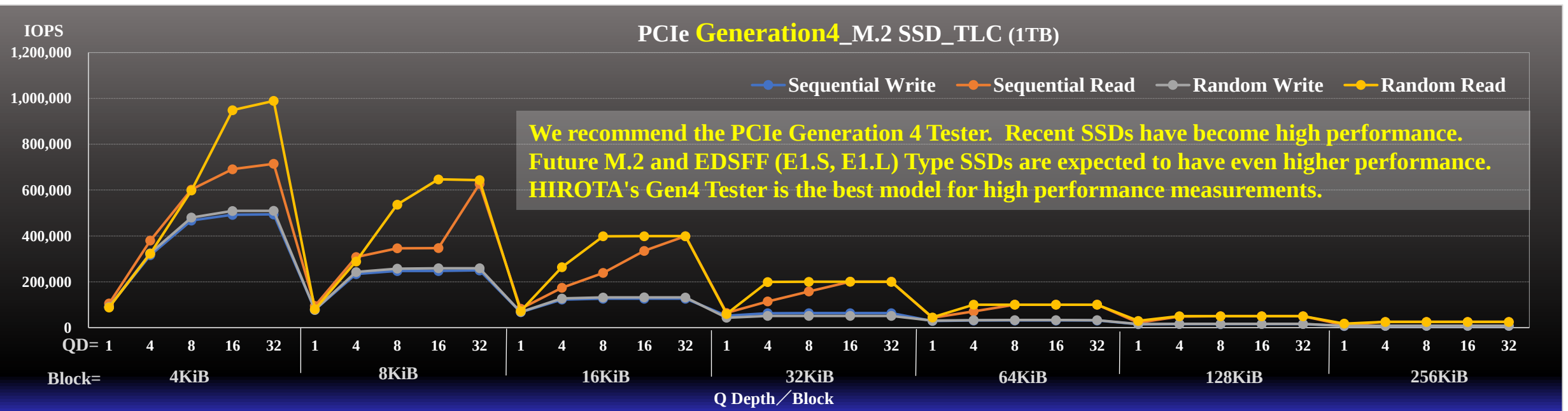
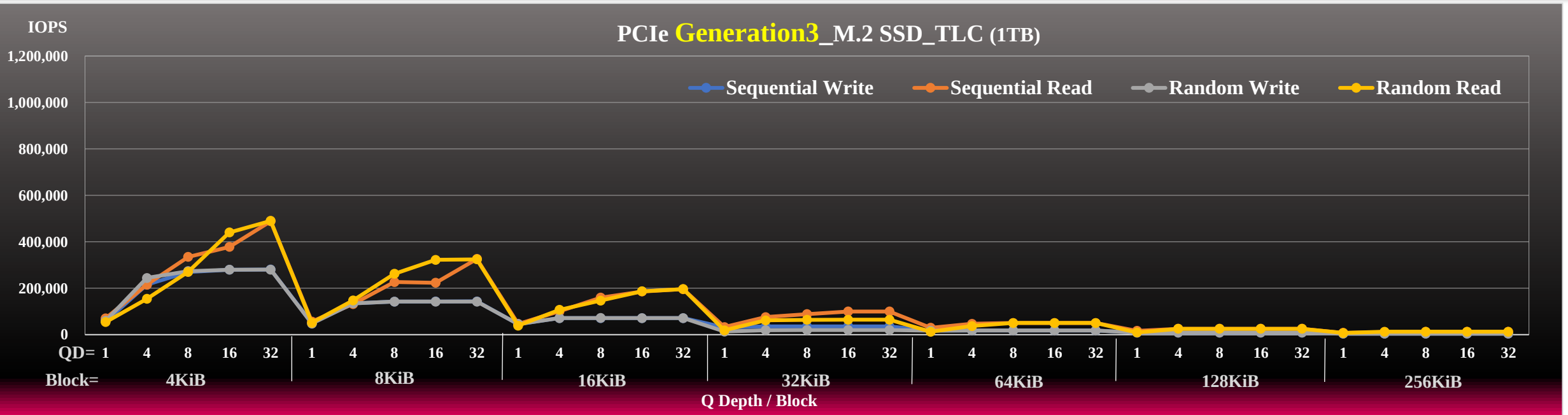
NVMe 1.4

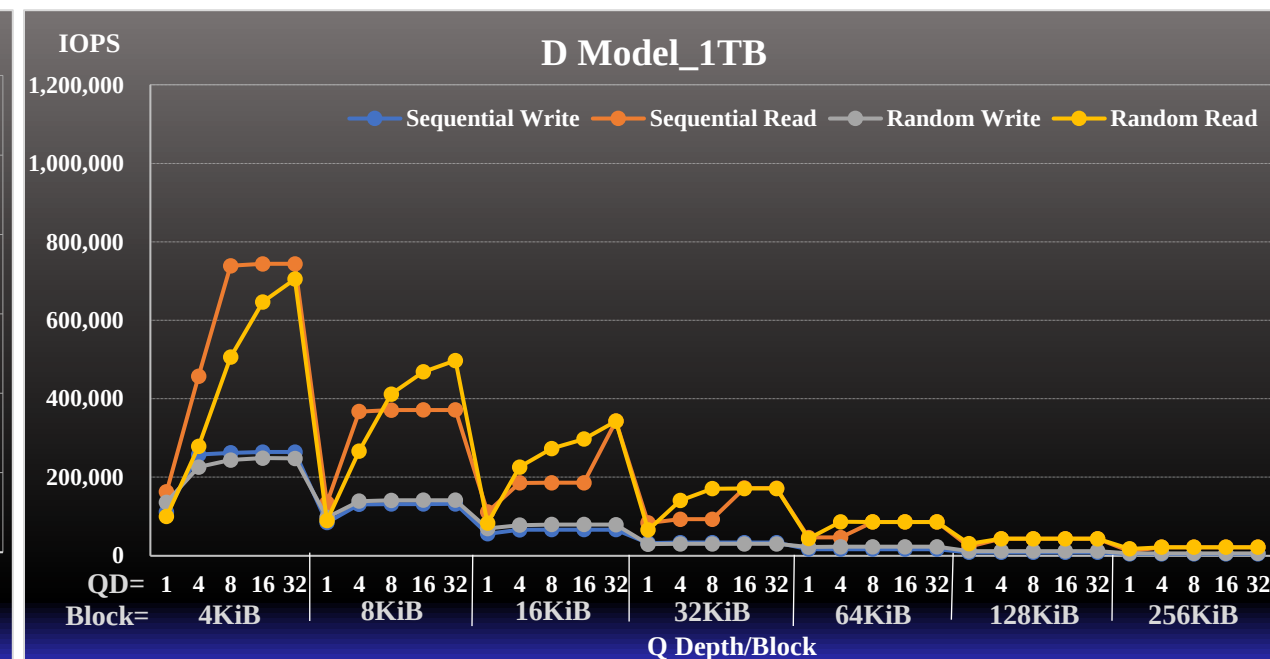
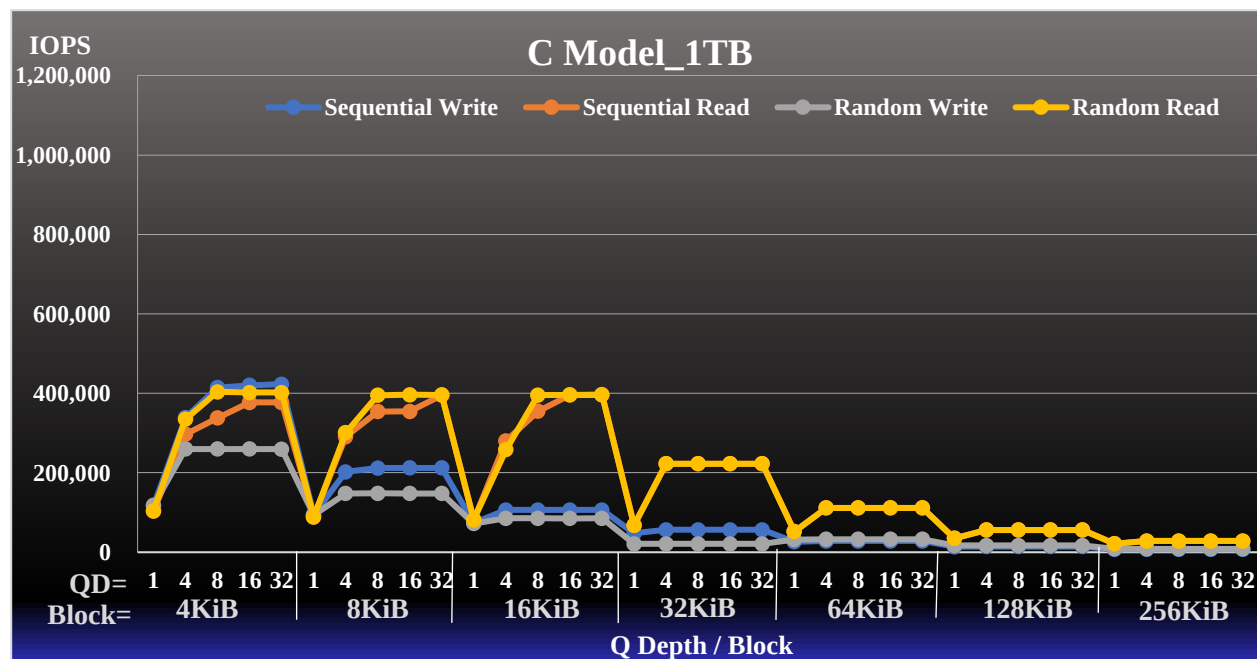
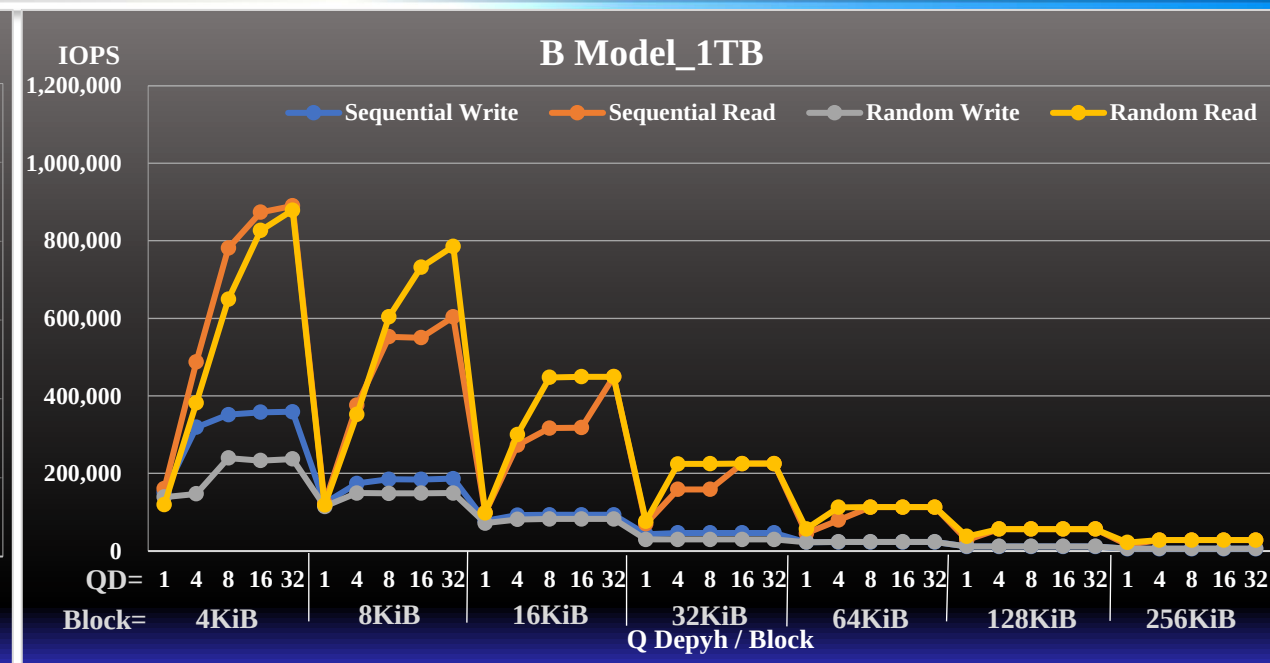
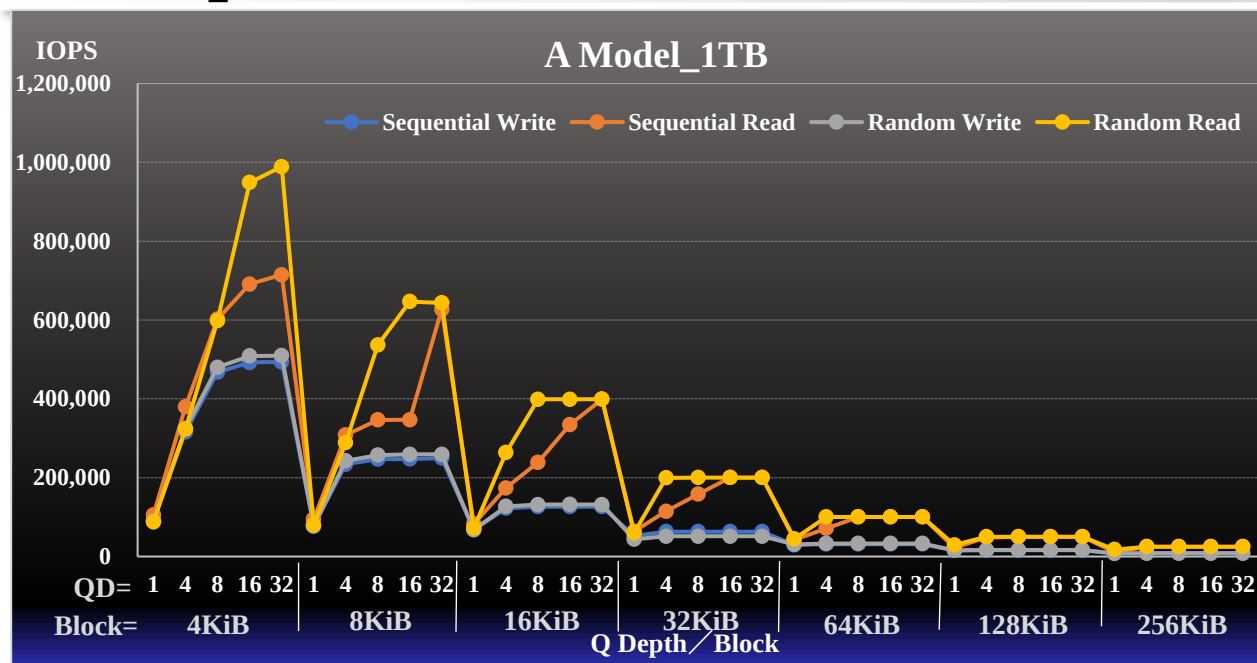


SMART TESTER for PCIe
【Support Interface PCIe Gen 3 x 4 Lane】



Example : Performance Evaluation, PCIe Gen3 vs Gen4 SSD





Size : Not include protrusions



Size: W460 x D420 x H350mm
M.2 SSD (2280) Connection Image

➤ One Unit Type

Model : H4PC-P4

Excellent compact design with built-in air cooling fan for SSD.

【 Support Foam Factor 】

Standard : Add in Card

Option : M.2, U.2, CFexpress card

~Not include conversion adapter~

➤ Separate Type

The control box and drive unit are separated.
Excellent compact design with built-in air cooling fan for SSD.

There are two type s of drive units that connect to the control box.

【Control Box】 (Tester)



Size : W340 x D325 x H180mm

➤ Add in Card Base Type

Model : H4PS-P4



M.2 SSD (2280) Connection Image

Size : W282 x D330 x H300mm

【Drive Units】

➤ EDSFF Type

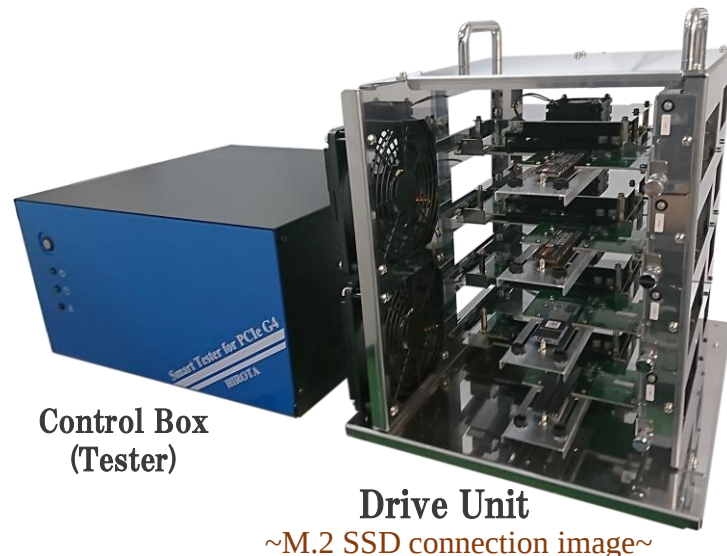
Model : H4PE-P4



Size : W300 x D440 x H300mm

Model : H4PS-P4

➤ Add in Card Base Type Drive Unit



Control Box Size: W340 x D325 x H180mm(Not include protrusions)
Drive Unit Size : W282 x D330 x H300mm(Not include protrusions)

【 Support Foam Factor 】

Standard : Add in Card

Option : M.2, U.2, CFexpress card

~Not include conversion adapter ~

Model : H4PE-P4

➤ EDSFF Type Drive Unit

~SSD (E1.L) connected image~



Control Box Size: W340 x D325 x H180mm(Not include protrusions)
Drive Unit Size : W300 x D440 x H300mm(Not include protrusions)

【 Drive Unit Structural Image 】

【 Support Foam Factor 】

【 E1.S, E1.L, E3.S 】

Standard

Back Plane Board

AIC

Built-in

Conversion Adapter

EDSFF



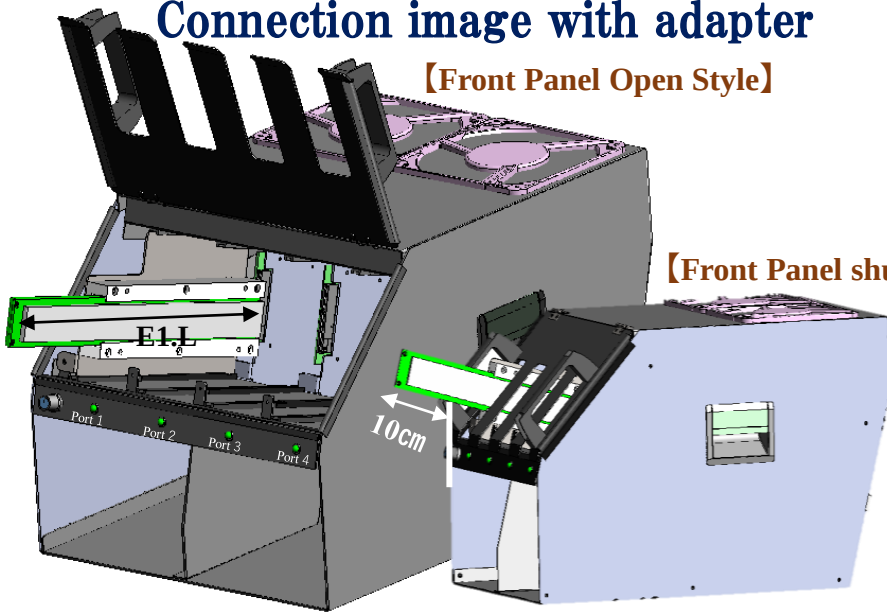
Each fixture can be set in the chamber to evaluate the temperature and humidity environment.

EDSFF Drive Unit Connection Image

E1.L

Connection image with adapter

【Front Panel Open Style】

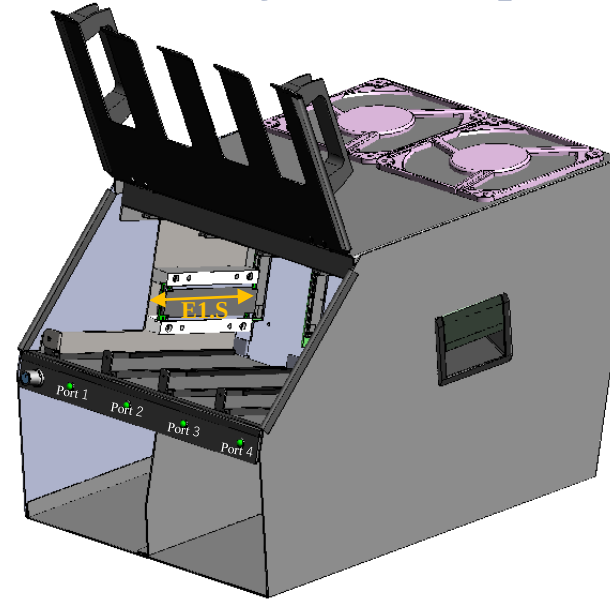


【Front Panel shut Style】

When user connect the E1.L SSD and shut the front panel, the SSD pops out about 10 cm.

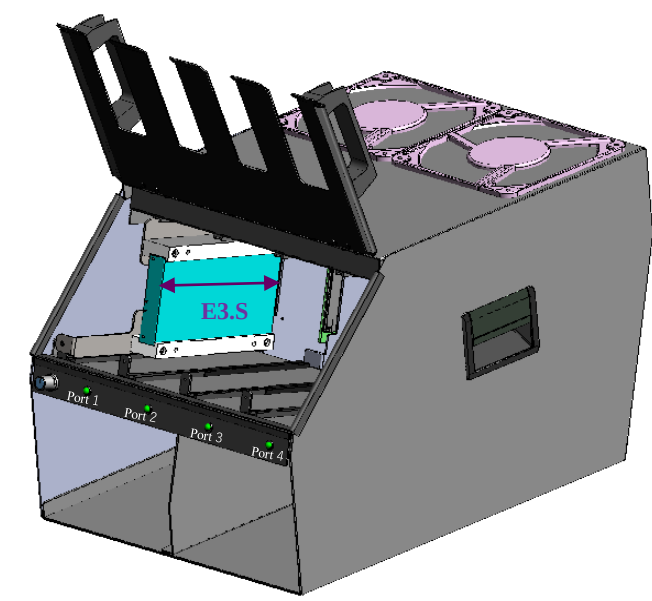
E1.S

Connection image with adapter



E3.S

Connection image with adapter

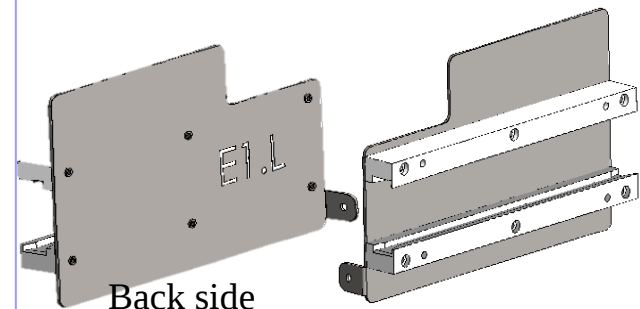


【SSD Hold Metal】

E1. L

Thickness: 9.5mm & 18mm

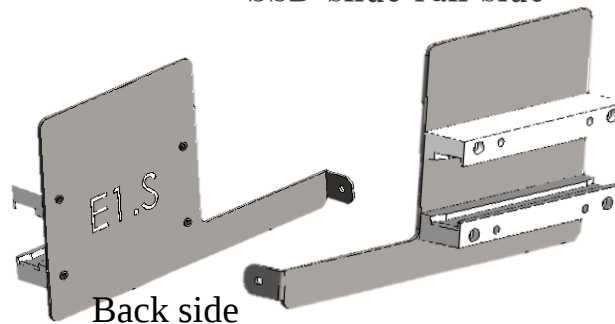
SSD slide rail side



E1. S

Thickness: 9.5mm & 25mm

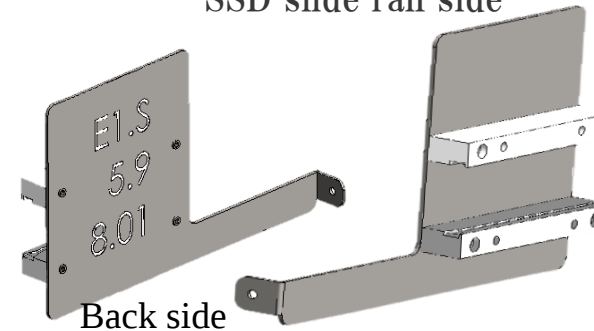
SSD slide rail side



E1. S

Thickness: 5.9mm & 8.01mm

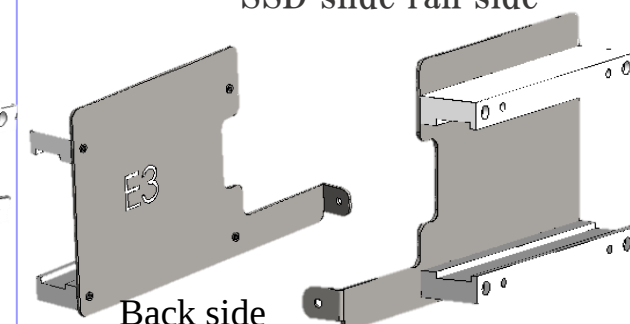
SSD slide rail side



E3. S

Thickness: 16.8mm

SSD slide rail side



※ Various adapters can be used on all ports. Various adapters for 4 ports are standard accessories. Housing material : Stainless steel (SUS430) without painting.

SMART TESTER for PCIe G3 Variation

EDSFF Drive Unit connection image.



➤ Control Unit

User can select various combinations of the Drive Unit for control unit.

Size : W250 x D330 x H140mm

Size : Not include protrusions



➤ Drive Unit (Fixture) Lineup

【 Horizontal Insertion Type 】

【 Multi Angle Type 】

【 M.2 Type 】

【 EDSFF Type 】

for M.2 SSD(2230-22110)

for E1.S, E1.L, E3.S



Standard : Add in Card

Option : M.2, U.2, CFexpress card

~Not include conversion adapter~

Size : W250 x D230 x H160mm



Size : W370 x D312 x H520mm



Size : W395 x D158 x H47mm



Size : W300 x D440 x H300mm

Customer introduction

TOSHIBA

Leading Innovation >>>

FUJITSU

Panasonic

HITACHI
Inspire the Next

SHARP

KIOXIA

PFU

a Fujitsu company

SONY

Nextorage

TEC



**MITSUBISHI
ELECTRIC**

Changes for the Better

Sodick

kingston

SEGA

RICOH
imagine. change.

FUJI xerox



KONICA MINOLTA

HAGIWARA Solutions

ハギワラソリューションズ株式会社

Canon OKI NEC

innodisk

Lexar

SanDisk

PHISON

Knows What You Need

Phison Electronics Corp.

進化する明日へ Continue thinking

I-O DATA

BUFFALO

**CORE
STORAGE**
合肥兆芯电子



Interface



株式会社立花エレクトック

brother
at your side

Schneider Electric

**SHOWA
DENKO**

ALLIION

Anritsu



明電舎

Ikegami

azbil

NHK ニッパツ
日本発条株式会社

EG E-Globaledge Corporation

OMRON



Seicomart

Thanks for Social Distancing



株式会社タカコム

第一興商

Issue a corresponding command for each protocol and execute flexible combination evaluation.

Flexible combination ↗↗

Professional function ↗↗



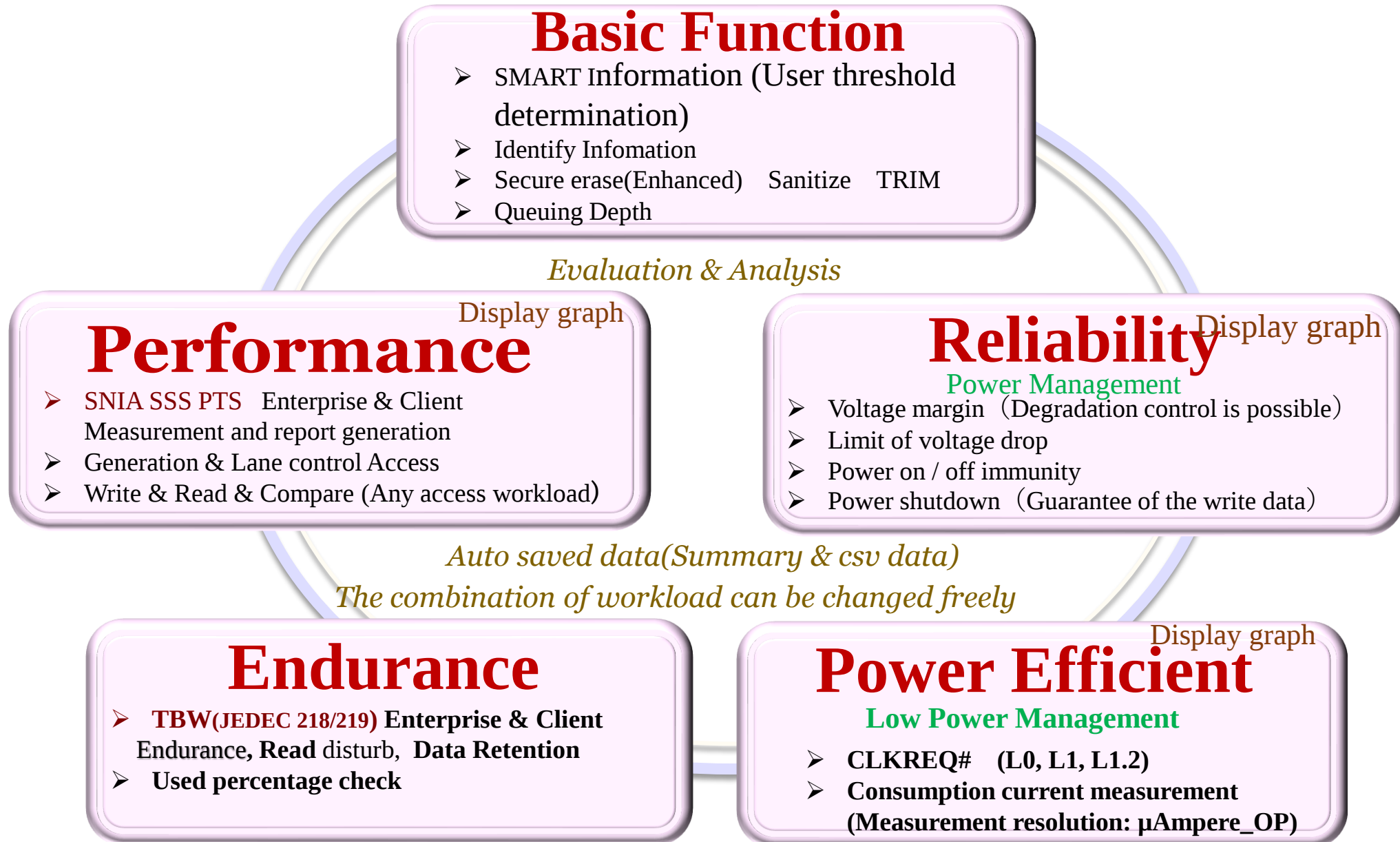
Double Method
Access

Standardization Test

- **TBW Test (Enterprise & Client)**
JEDEC218/219
 - Endurance • Data Retention • Read Disturb
- **SNIA SSS PTS (Enterprise & Client)**
Performance Test for Steady State

Vendor Unique Test

- **Flexibility Test**
 - Performance • Endurance • Power Management
 - Low Power Management
- **Visualization by graph display**
 - Performance • Power



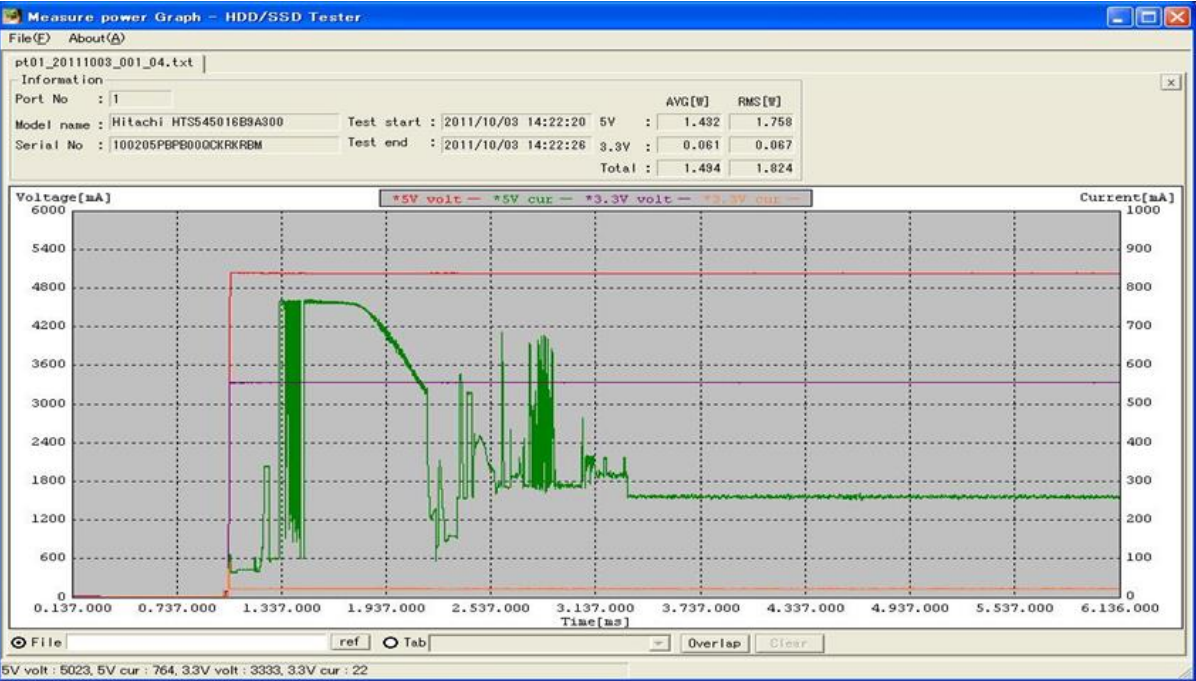
Tester Basic Specifications

Item	SMART TESTER for PCIe (Generation 3)	SMART TESTER for PCIe G4 (Generation 4)		
Model	H4PR-P3F4	H4PC-P4	H4PS-P4	H4PE-P4
Interface	PCIe Gen-1 (2.5Gbps) ~ Gen-3 (8.0Gbps)	PCIe Gen-1 ~ Gen-4 (16Gbps) 4 Lane ~ Controllable ~		
Lane	4 Lane ~ Controllable ~			
Connect port	4port/Tester Expandable with Cascade Connection			
Protocol Ver.	NVMe1.3, AHCI	NVMe 1.4		
Memory	8GB/Tester, I/F buffer:64MB/port	32GB/Tester, I/F buffer : 4GB/port		
SM Bus	—	○	○	○
Hot plug	○	○	○	○
UART	○	○	○	○
Foam Factor	Standard : Add in Card Type Connector	OP : U.2, M.2(2230-22110), CFexpress card		EDSFF (L1.S, L1.L, E3.S)
Power Supply	AC95~242V 47/63Hz			
Environment	Ambient Temperature: 20℃~40℃, Ambient Humidity :20~80%RH, * No condensation exists.			
Outer Dimensions	W370*D310*H530mm (Multi angle model)	W420*D460*H350mm	Tester:W340*D325*H180mm D U:W282*D330*H300mm	Tester:W340*D325*H180mm DU:W300*D440*H300mm

- 【Memo】
1. Not include OP conversion adapter .
 2. The FESFF Drive Unit is also available in Gen 3 Type. Please contact us for details.

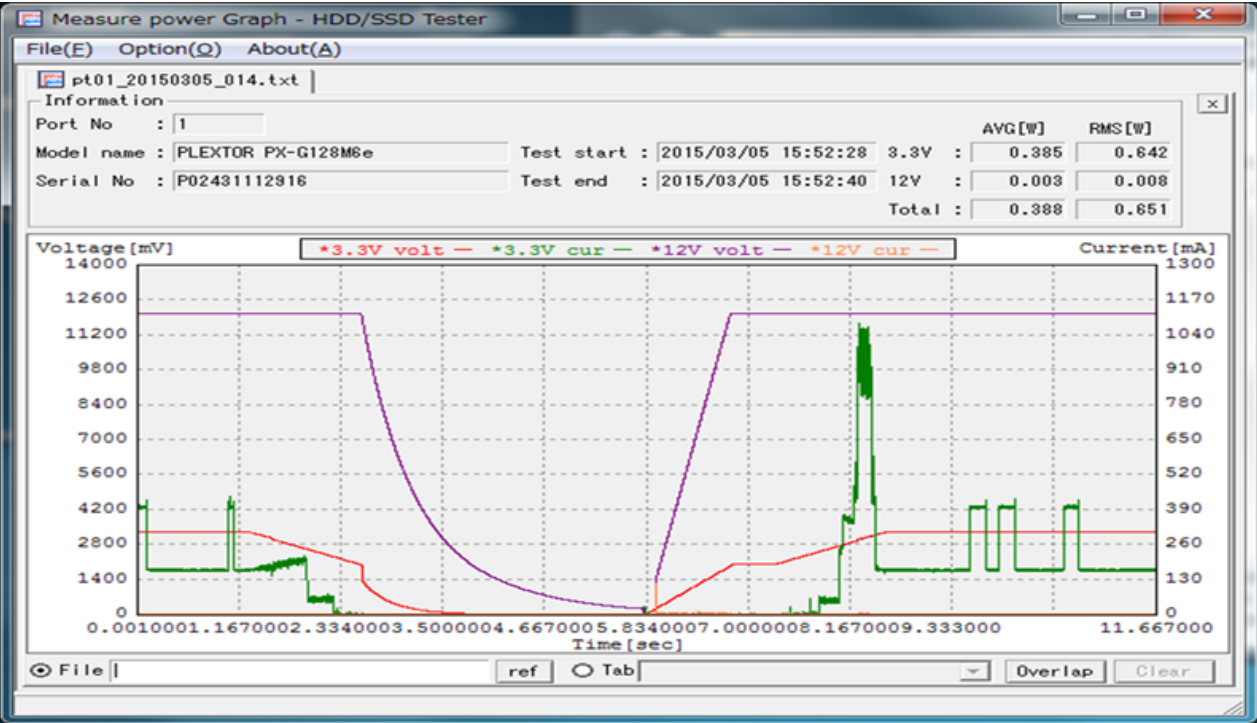
項目	概要
Drive Power Supply	+12V Variable range : 8.0V to 14.5V (20mV step pitch) Voltage accuracy : $\pm 100\text{mV}$ Max current : 3.5A +3.3V Variable range : 2.0V to 4.0V (10mV step pitch) Voltage accuracy : $\pm 50\text{mV}$ Max current : 4.2A
Detection of Excessive Drive Supply Voltage	+12V $15.2\text{V} \pm 3\%$ +3.3V $4.6\text{V} \pm 3\%$ Power off the detect port drive, when detect the overvoltage detection.
Measurement of Drive Power Supply Voltage	+12V measure range 0.0V to 15.0V measure accuracy $\pm 3\%\text{F.S}$ +3.3V 0.0V to 5.0V measure accuracy $\pm 3\%\text{F.S}$ Resolution : $3.3\text{V} \div 3.5\text{mV}$ $12\text{V} \div 7.9\text{mV}$ Sampling rate 125μsec to 0.2sec (125μs step) Sampling memory 65,520 data / port
Measurement of Drive Power Supply Current	+12V measure range 0.0A to 4.0A measure accuracy $\pm 3\%\text{F.S}$ +3.3V 0.0A to 5.0A measure accuracy $\pm 3\%\text{F.S}$ Resolution : $3.3\text{V} \div 2.6\text{mA}$ $12\text{V} \div 2.0\text{mA}$ Sampling rate 125μsec to 0.2sec (125μs step) Sampling memory 65,520 data / port
CLKREQ #	L1.2 level $\Rightarrow$ Micro current measurement: μA (Option) (Power saving transition level: $\text{L0} \succ \text{L1} \succ \text{L1.2}$)

Example of Current & Voltage Measurement



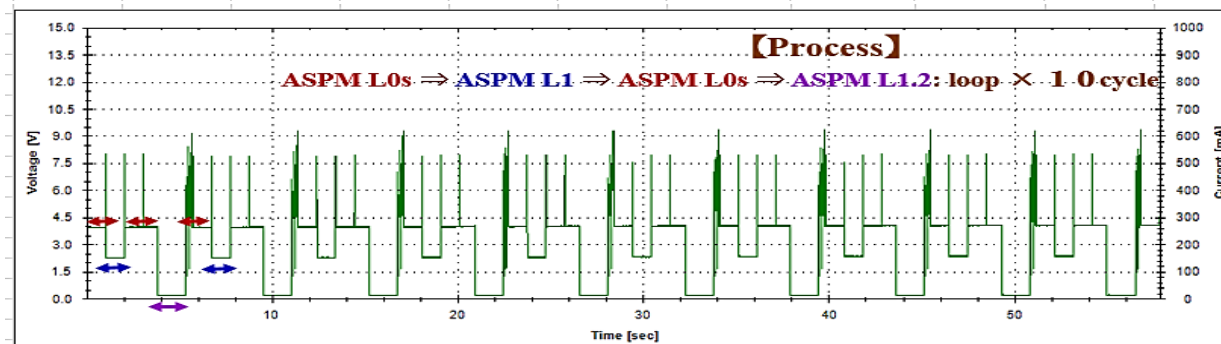
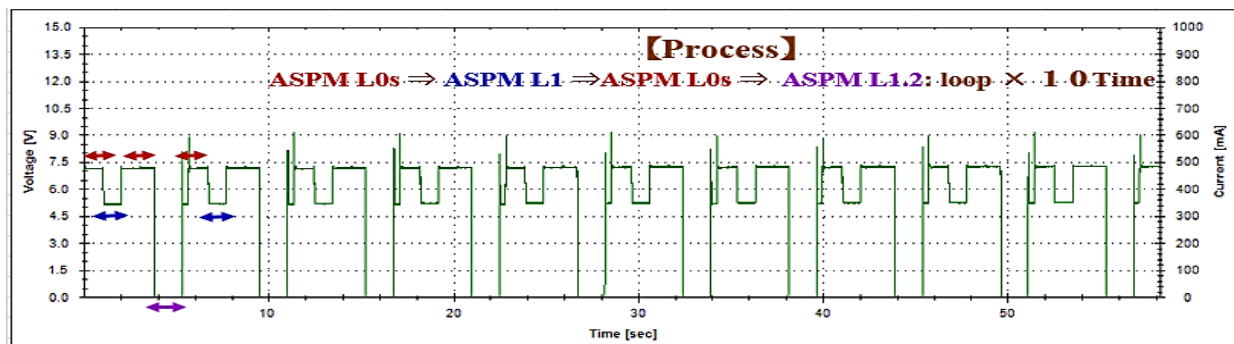
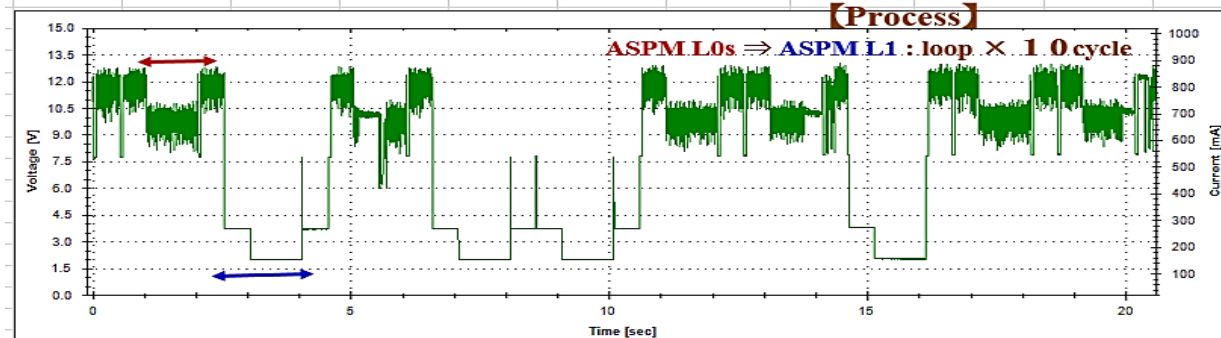
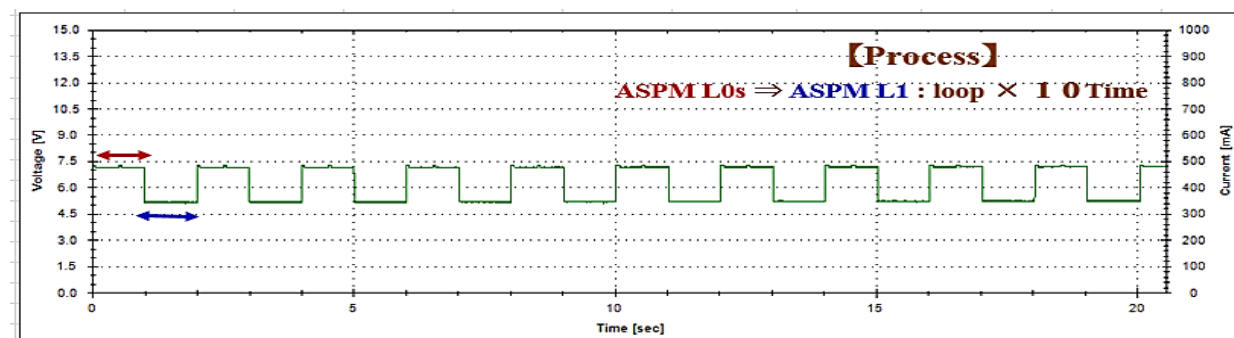
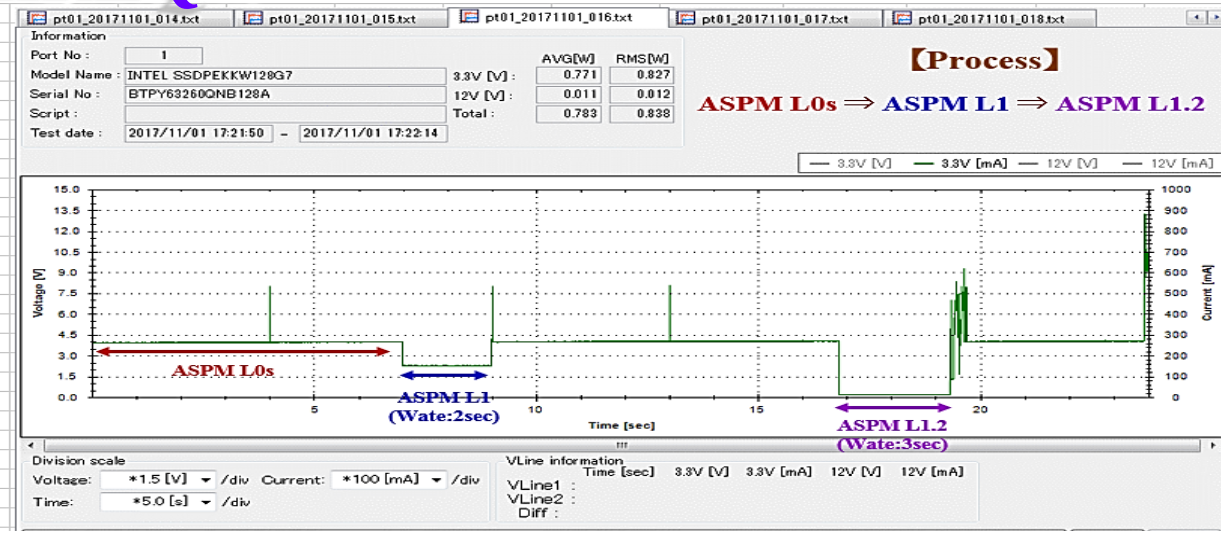
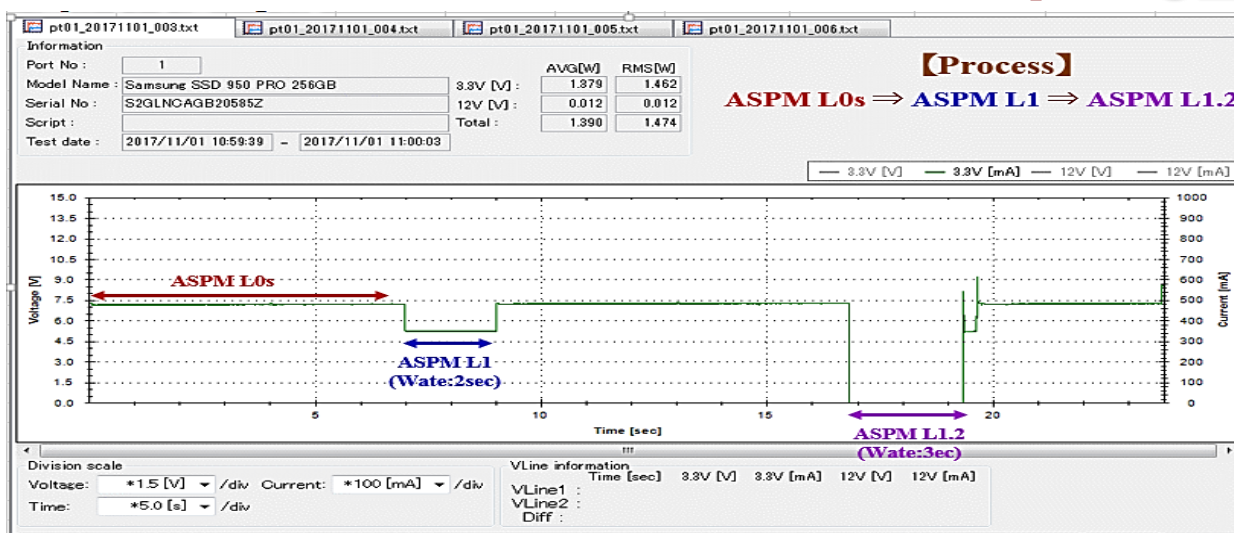
Wave at Power ON

Wave at Power OFF - ON



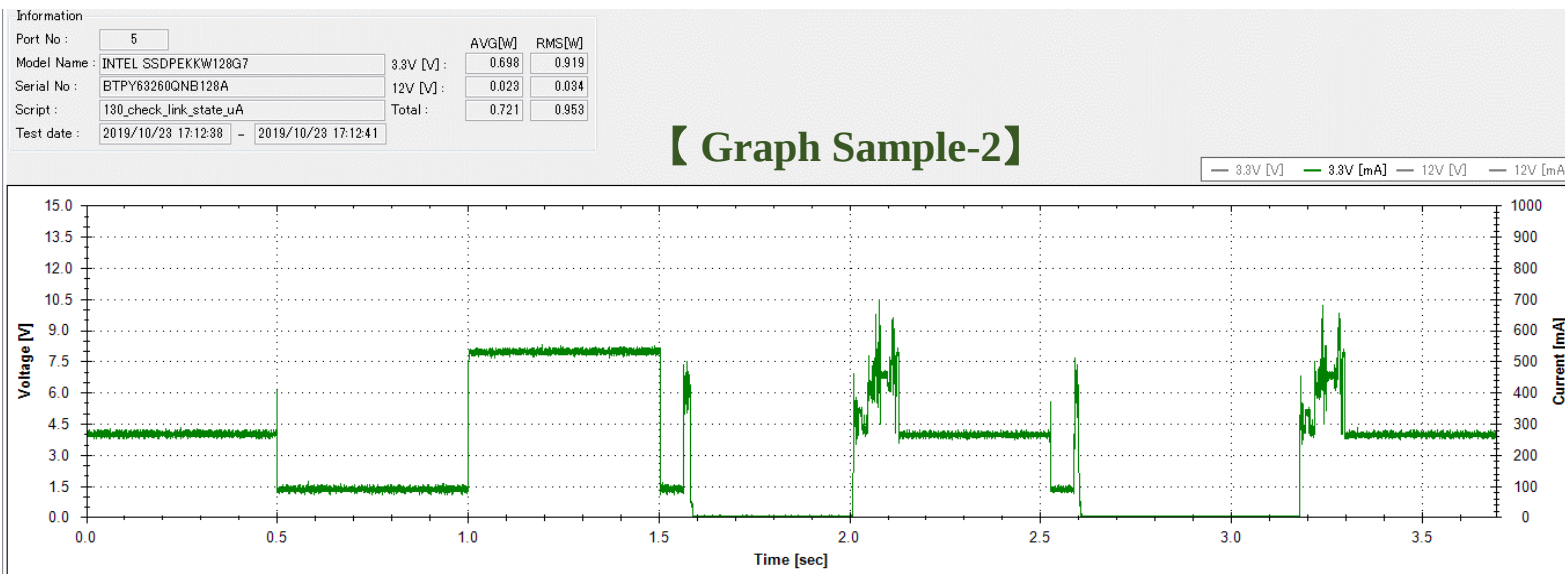
Low Power Measurement [Sample] CLKREQ

PCIe Type



【処理内容】 Idle ⇒ L1 ⇒ L1.1 ⇒ L1.2 ステートの遷移と電流値を確認

Resolution : μA



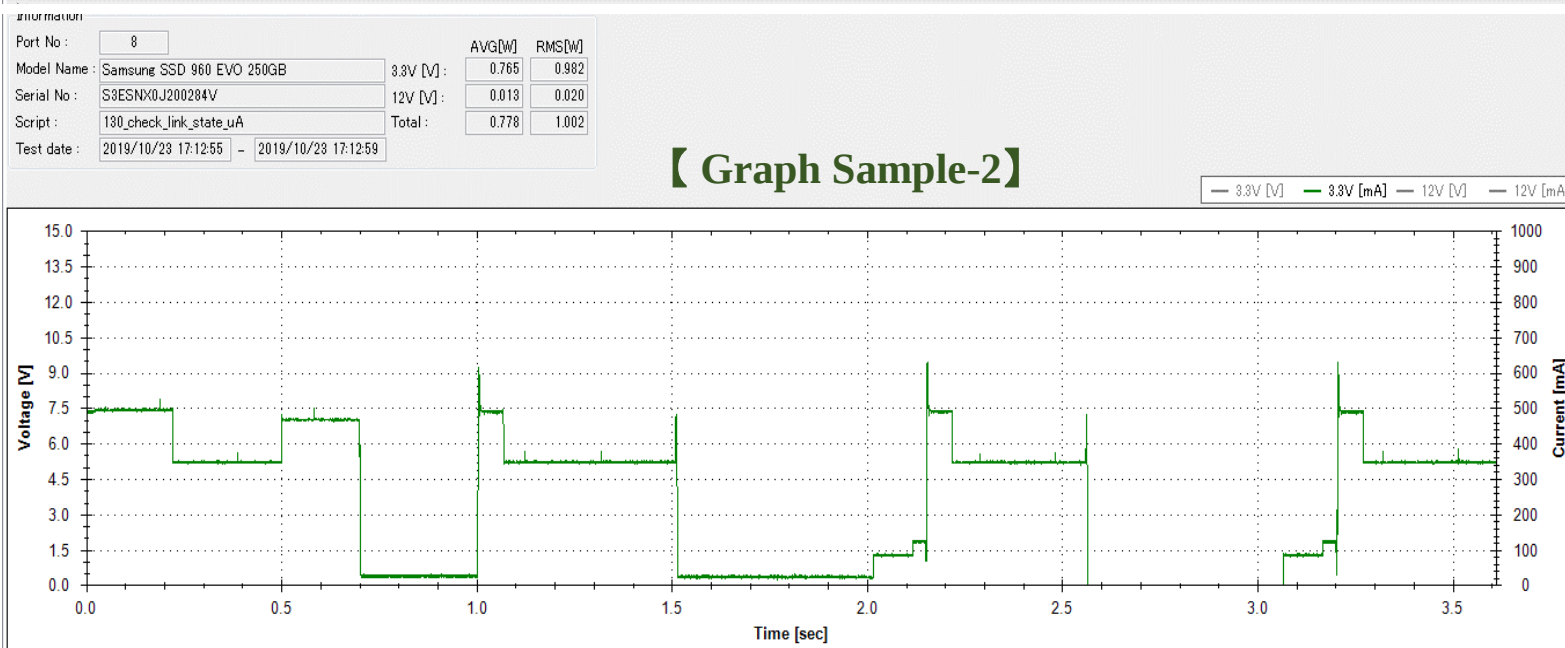
【 Summary Sample-1】

```
*****
power management features support info
*****
Number of Power States Support: 0x0004
ASPM L0s :not support
ASPM L1 :support
ASPM L1.1:support
ASPM L1.2:support
PM L1.1 :support
PM L1.2 :support
*****
[sec.msec.usec] power management features operate log
*****
[00.036.861] IDLE Stat Electric Current : 266[mA]

[00.536.894] ASPM L1.0 State In
[00.787.671] ASPM L1.0 Electric Current : 90[mA]
[01.039.525] ASPM L1.0 State Out

[01.540.441] ASPM L1.1 State In
[01.794.063] ASPM L1.1 CLKREQ# Signal state: 1
[01.794.524] ASPM L1.1 Electric Current : 1673[uA]
[02.047.183] ASPM L1.1 CLKREQ# Signal state: 0
[02.047.198] ASPM L1.1 State Out

[02.562.941] ASPM L1.2 State In
[02.817.266] ASPM L1.2 CLKREQ# Signal state: 1
[02.817.700] ASPM L1.2 Electric Current : 987[uA]
[03.216.873] ASPM L1.2 CLKREQ# Signal state: 0
[03.216.889] ASPM L1.2 State Out
```



【 Summary Sample-2】

```
*****
power management features support info
*****
Number of Power States Support: 0x0004
ASPM L0s :not support
ASPM L1 :support
ASPM L1.1:support
ASPM L1.2:support
PM L1.1 :support
PM L1.2 :support
*****
[sec.msec.usec] power management features operate log
*****
[00.036.872] IDLE Stat Electric Current : 488[mA]

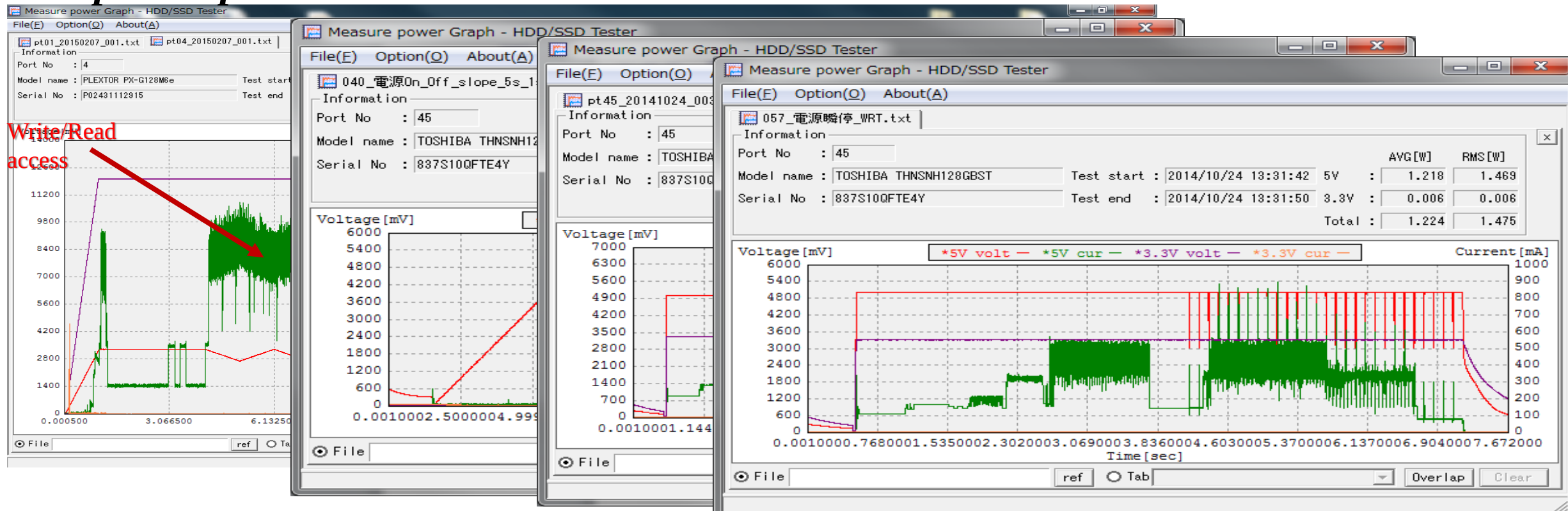
[00.536.899] ASPM L1.0 State In
[00.788.831] ASPM L1.0 Electric Current : 25[mA]
[01.045.932] ASPM L1.0 State Out

[01.547.797] ASPM L1.1 State In
[01.801.618] ASPM L1.1 CLKREQ# Signal state: 1
[01.801.909] ASPM L1.1 Electric Current : 22000[uA]
[02.054.099] ASPM L1.1 CLKREQ# Signal state: 0
[02.054.113] ASPM L1.1 State Out
[02.598.307] ASPM L1.2 State In
[02.851.765] ASPM L1.2 CLKREQ# Signal state: 1
[02.852.253] ASPM L1.2 Electric Current : 993[uA]
[03.104.329] ASPM L1.2 CLKREQ# Signal state: 0
[03.104.344] ASPM L1.2 State Out
```

- Assume a bad power supply, oscillation, noise, etc., and execute a simulation test.
- Supports toggle function and up / down slope control function.
- The measured data can be graphed in real time and confirmed.

◆ Voltage margin +12V Variable range : 8.0V to 14.5V (20mV step pitch)
+3.3V Variable range : 2.0V to 4.0V (10mV step pitch)

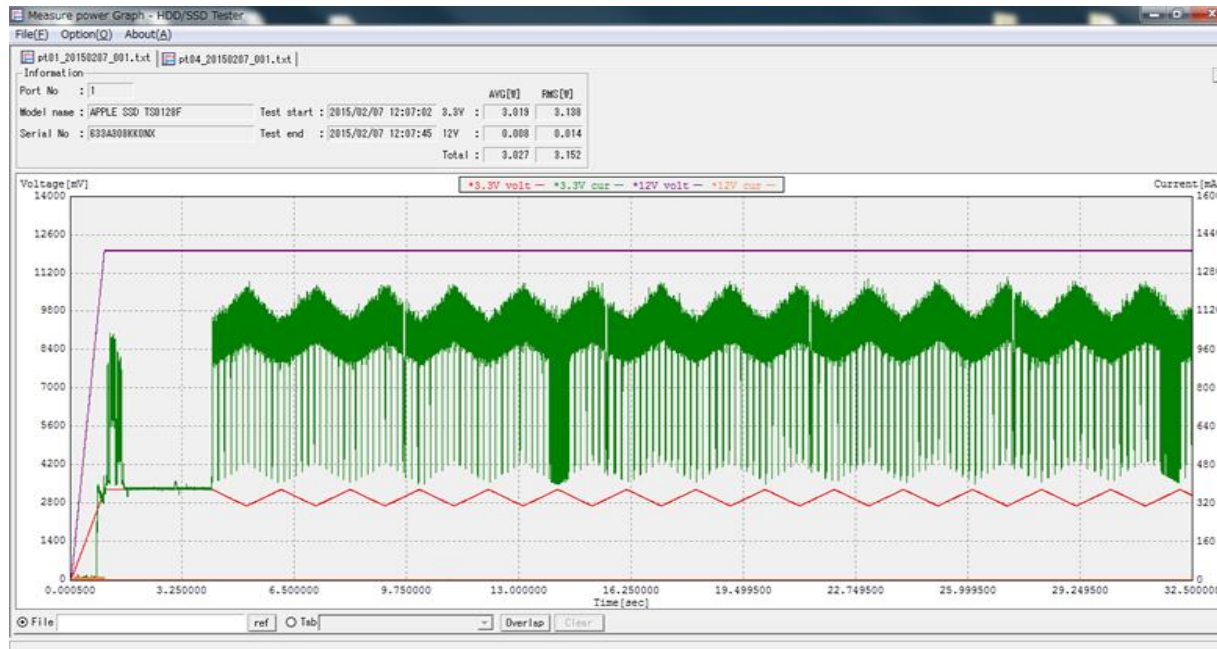
Sample Graph



A Model

Benchmarking with
the same condition

B Model Drive



Capable of measuring **the current** while varying **the voltage**.

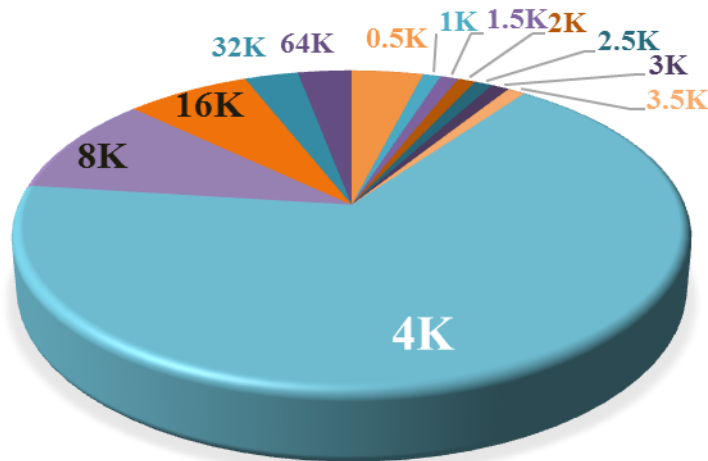
➤ B Model was reset by the voltage drop under unstable voltage environment.

◆ Voltage margin • +12V Variable range : 8.0V to 14.5V (20mV step pitch) • +3.3V Variable range : 2.0V to 4.0V (10mV step pitch)

Endurance Test

◆ for Enterprise Model

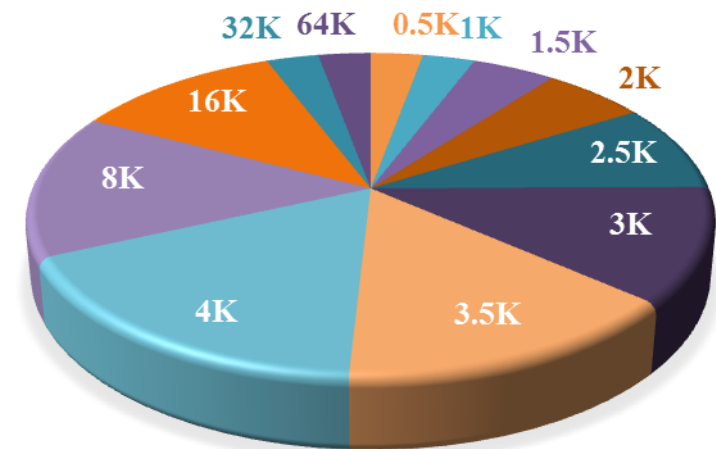
Standard Ratio Access



Access conditions are changeable.

- ◆ Transfer Brock Length
- ◆ Access share (by random Access)

Flexible Ratio Access
(Original Script)



◆ for Client Model

The test scripts are available in accordance with JEDEC Standard, 【JESD 218A】

Data Retention Test, Read Disturb Test, the script is already prepared.

【 Ref 】 Data Retention Test is keep it in a temperature control Chamber without power supply temperature: 125 °C
Leave time: client SSD = 336 H Enterprise SSD = 504 H

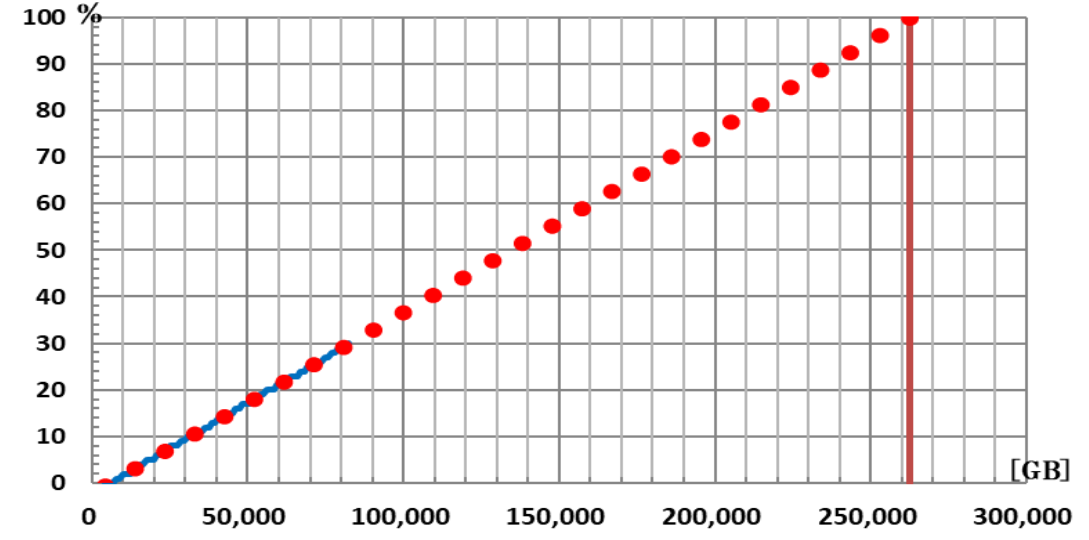
TBW Predictive Evaluation

* Running Log *

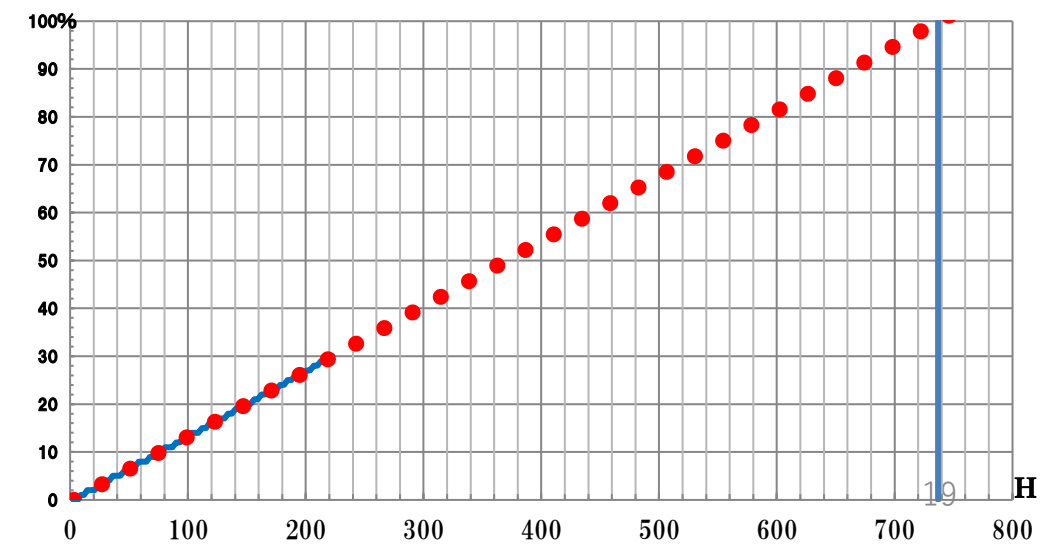
Elapsed Time [day:h:m:s]	Count	Endurance Indicator [%]	Total WR in test [TiB]	Written Statistics [TiB]	Rate [MB/s]
000:00:18:42	1	1	0.4	0	456
000:00:37:38	2	1	0.9	0	450
000:00:56:18	3	1	1.3	0	457
000:01:14:56	4	1	1.8	0	458
000:01:33:33	5	2	2.3	0	458
000:01:52:12	6	2	2.7	0	457
000:02:10:51	7	2	3.2	0	457
000:02:29:30	8	2	3.7	0	457
000:02:48:11	9	2	4.1	0	456
000:03:06:52	10	2	4.6	0	456
000:03:25:32	11	2	5.1	0	457
000:03:44:19	12	2	5.5	0	454
000:04:03:03	13	2	6.0	0	455
000:04:21:41	14	2	6.5	0	458
000:04:40:23	15	2	6.9	0	456
000:04:59:02	16	2	7.4	0	457
000:05:17:39	17	2	7.9	0	458
000:05:36:19	18	2	8.3	0	457
000:05:54:55	19	3	8.8	0	458
000:06:13:33	20	3	9.3	0	458
000:06:32:15	21	3	9.7	0	456
000:06:50:56	22	3	10.2	0	456
000:07:09:36	23	3	10.7	0	457
000:07:28:19	24	3	11.1	0	456
000:07:47:03	25	3	11.6	0	455
000:08:05:40	26	3	12.1	0	458
000:08:24:17	27	3	12.5	0	458
000:08:42:55	28	3	13.0	0	458
000:09:01:38	29	3	13.5	0	456
000:09:20:20	30	3	13.9	0	456
000:09:39:04	31	3	14.4	0	455
000:09:57:43	32	3	14.8	0	457
000:10:16:25	33	3	15.3	0	456
000:10:35:02	34	4	15.8	0	458
000:10:53:43	35	4	16.2	0	456
000:11:12:29	36	4	16.7	0	454
000:11:31:08	37	4	17.2	0	457

NVMe xxx Model 512GB Sample Graph

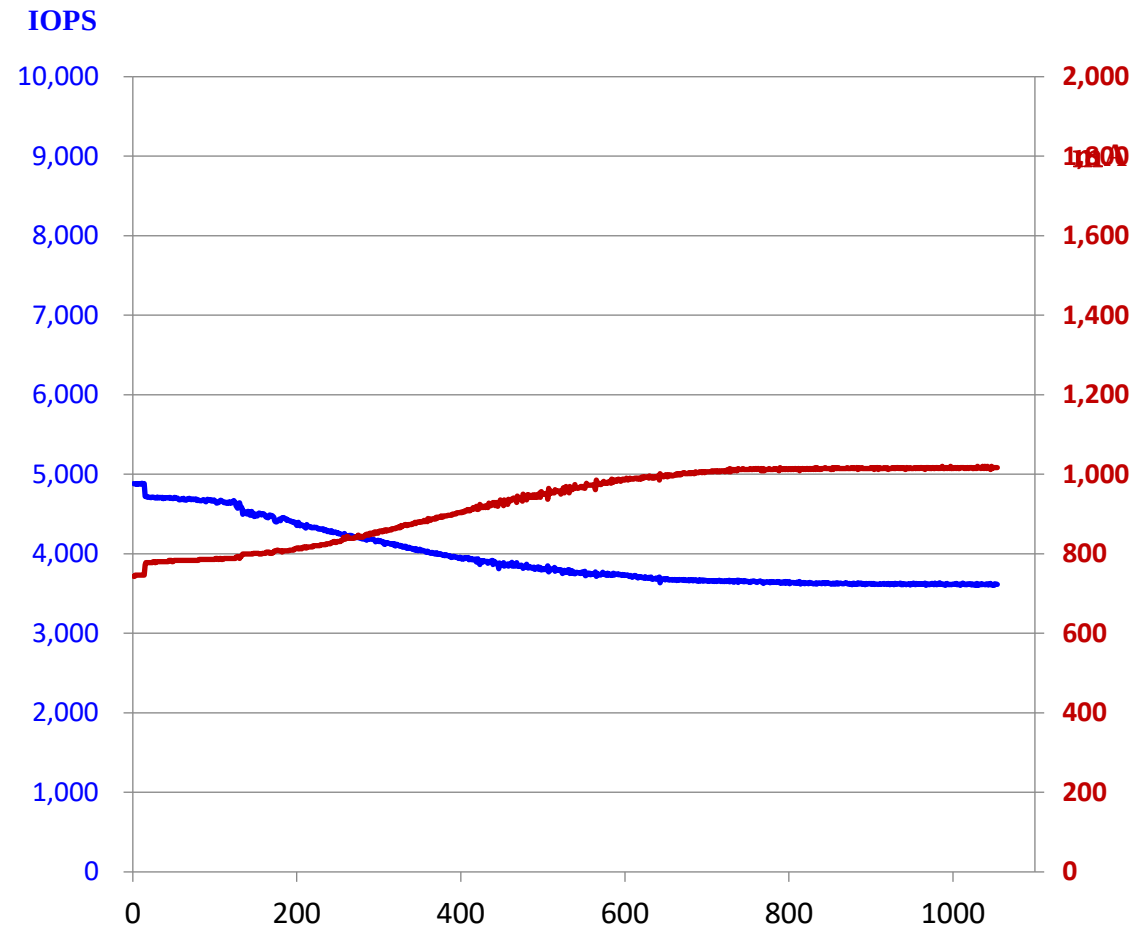
【Writing capacity prediction】



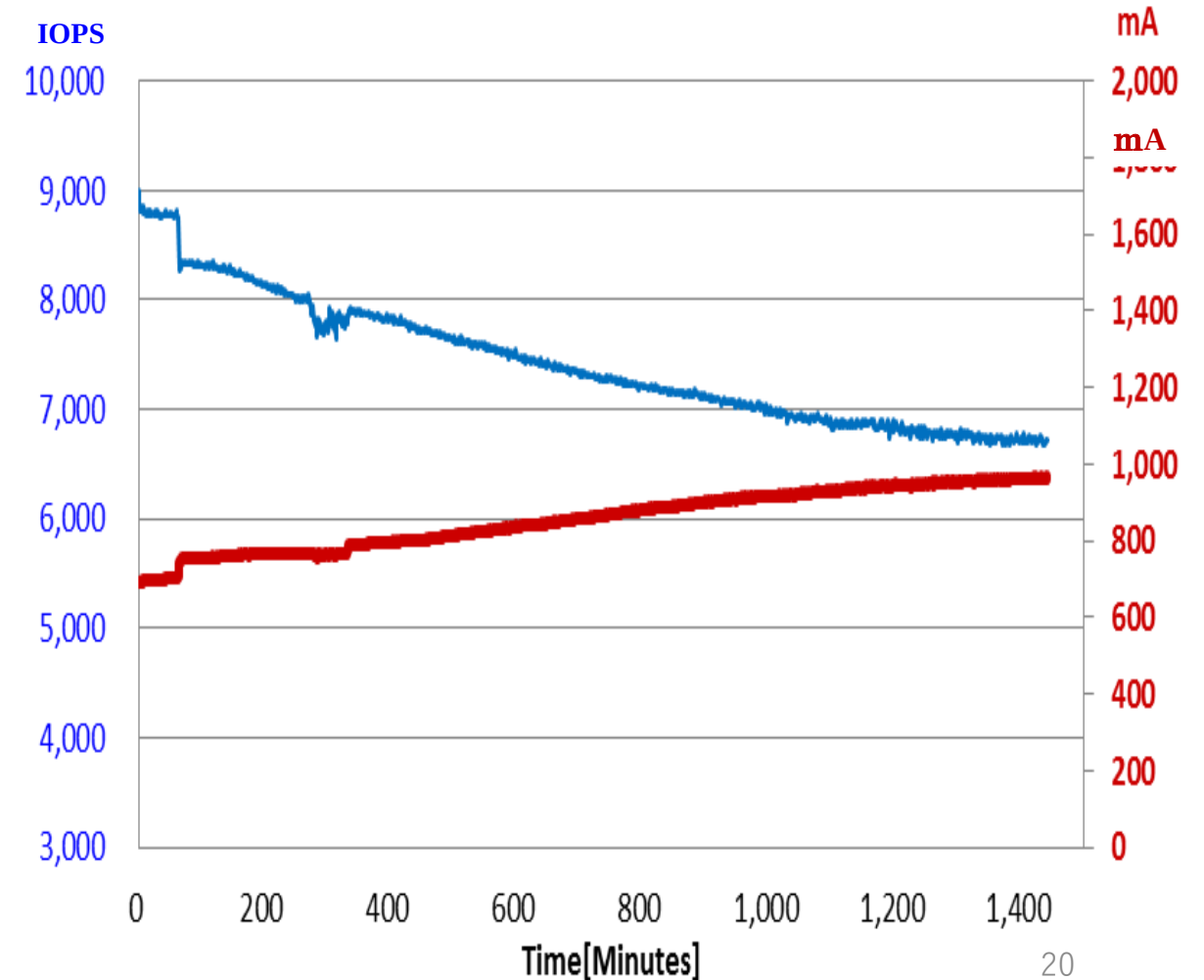
【Writing time prediction】



NVMe xxx Model Sample Graph



NVMe xxx Model Sample Graph



テスト 項目	概 要
IOPS IOPS Test	We measure and analyze IOPS (Input / Output per second) down to Steady State based on seven kinds of Read/Write combinations and eight kinds access block sizes (=56 kinds combinations)
TP Throughput Test	We measure and analyze the throughput down to Steady state in two block sizes of 1024KiB and 128KiB.
Latency Latency Test	We measure and analyze the Average Latency and Maximum Latency in three kinds combinations of Read / write and three kinds access block sizes.
Write Saturation Write Saturation Test	We measure and analyze IOPS drop compare with writing time or TGBW(Total GiB Byte Written). The evaluation starts from 24 hours after FOB state or after achieved four times SSD capacity writing.
HIR Host Idle Recovery Test	We measure SSD performance affection of continuous writing performance in small blocks (4KiB Random) by host IDLE time.
XSR Cross Stimulus Recovery Test	We measure and analyze the performance affection at write access switch timing from SEQ(1024KiB) to RND(8KiB) and from RND(8KiB) to SEQ(1024KiB).
CBW Composite Block Size Workload Test	We measure the performance under mixed ten work loads which is not simple transfer length like RND 4KB.
DIRTH Demand Intensity / Response Time Histogram Test	We can create the histogram of IOPS vs operating time related to two kinds work loads.

【About SNIA】

SNIA is **Storage Networking Industry Association** which is the largest storage network industry association.

【SSS PTS】

SSS PTS : **Solid State Storage Performance Test Specification**

Measure the performance of the SSD that reached steady state with the specified workload.

Outputs the obtained measurement result in specified report format.

【Merit】



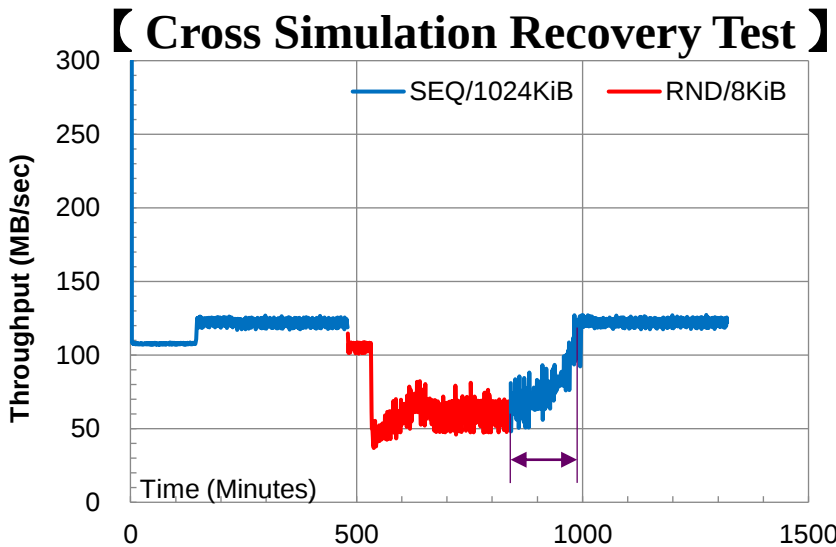
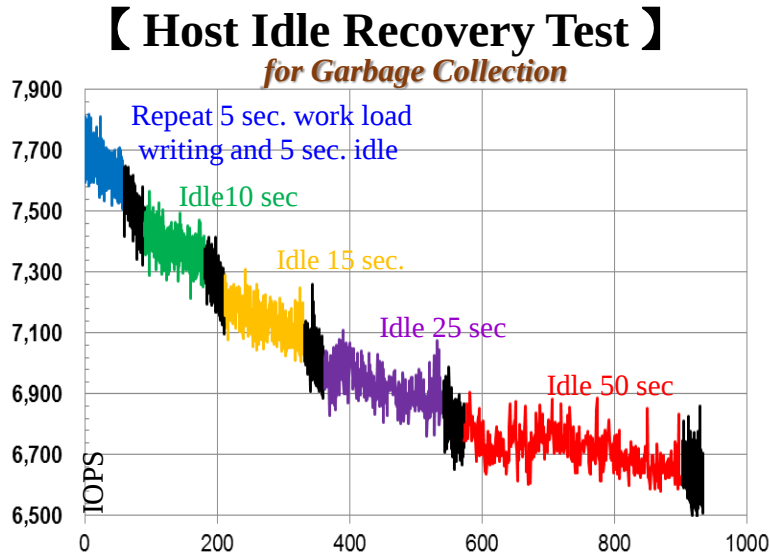
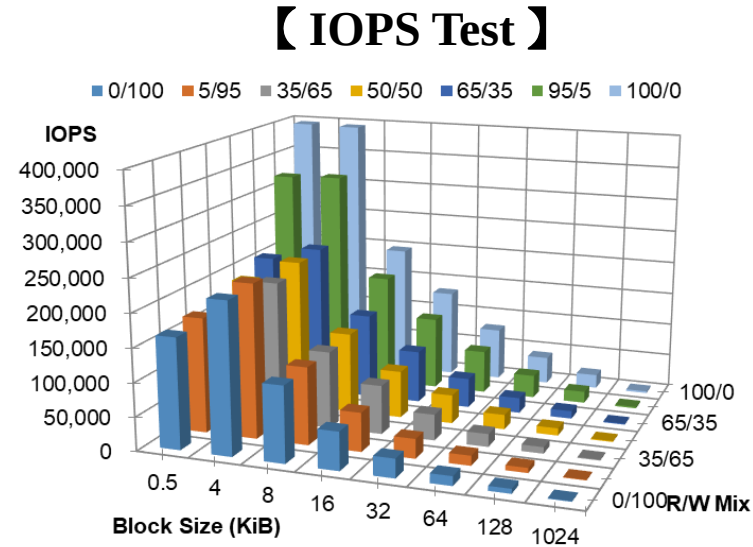
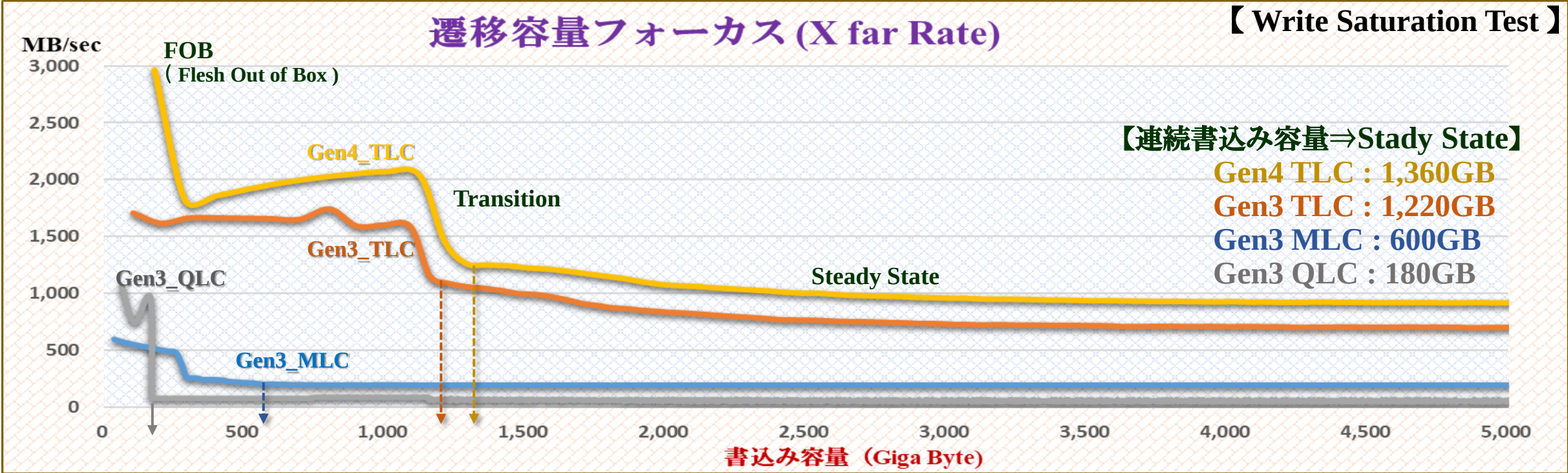
Objective comparative evaluation of SSDs with world standard specifications

It can see the marginal performance of the SSD in just one day

It can objectively compare and evaluate SSD according to the prescribed method

Automated by dedicated script and it can be evaluated efficiently

Various result report such as three dimensional graph can be issued automatically



Thank you.



Please feel free to contact us.

【 Sales representative 】

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CFA
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